

**IN THE SPECIFICATION**

**Please amend the paragraph beginning on page 1, line 6 as follows:**

This application is a Divisional of U.S. Application No. 10/137,499 filed May 2, 2002, now U.S. Patent No. 7,045,430, which is incorporated herein by reference.

**Please amend the paragraph beginning on page 1, line 8 as follows:**

This application is related to the following, co-pending, commonly assigned applications, incorporated herein by reference:

U.S. Application Serial No. 10/081,439, entitled: "Evaporated LaAlO<sub>3</sub> Films for Gate Dielectrics," now U.S. Patent No. 6,893,984,

U.S. Application Serial No. 10/137,058, entitled: "Atomic Layer Deposition and Conversion,"

U.S. Application Serial No. 10/137,168, entitled: "Atomic Layer of AlO<sub>x</sub> for ULSI Gate Atomic Layer Deposition for Gate Dielectric Layer," now U.S. Patent No. 7,160,577, and

U.S. Application Serial No. 09/797,324, entitled: "Methods, Systems, and Apparatus for Uniform Chemical-Vapor Depositions[["],]" now U.S. Patent No. 6,852,167.

**Please amend the paragraph beginning on page 20, line 14 as follows:**

In accordance with the present invention, a LaAlO<sub>3</sub> film, for example, layer 441 of Figure 4, for use as a gate dielectric forms on body region of a transistor by the ALD process using a lanthanum/ozone/aluminum/water cycle. This cycle is the combination of a lanthanum/ozone sequence and an aluminum/water sequence. Terminating the cycle at the end of a lanthanum/ozone sequence would result in a La<sub>2</sub>O<sub>3</sub> film. Performing just an aluminum/water sequence would result in an Al<sub>2</sub>O<sub>3</sub> film, for example, layer 443 of Figure 4.